L Number	Hits	Search Text	DB	Time stamp
-	558920	capacitor	USPAT;	2004/02/06 11:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4784	capacitor and ((first adj conduct\$4) with substrate)	USPAT;	2004/02/06 11:51
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	98978	capacitor and memory	USPAT;	2004/02/06 11:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/00 44 54
-	2639	(capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 11:51
		substrate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	407	1/ 1/ 1/ 1/ 1/ 1/ 1/ 1/ 1/ 1/ 1/ 1/ 1/ 1	IBM_TDB	0004/00/00 44-54
-	167	((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 11:54
		substrate)) and ((silicon adj nitride) with (first adj conduct\$4))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			· ·	
	64	(((capacitor and memory) and ((first adj conduct\$4) with	IBM_TDB USPAT;	2004/02/06 11:59
-	04	substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	2004/02/00 11.59
		conduct\$4))) and (first near2 oxide)	EPO; JPO;	
		Conducty+/// and (mst near2 oxide)	DERWENT;	
			IBM_TDB	
_ '	33	((((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 11:58
		substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	
		conduct\$4))) and (first near2 oxide)) and ((silicon adj nitride)	EPO; JPO;	
		with (first near2 oxide))	DERWENT;	
1			IBM_TDB	
_	17	(((((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 12:00
		substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	
		conduct\$4))) and (first near2 oxide)) and ((silicon adj nitride)	EPO; JPO;	
		with (first near2 oxide))) and (second near2 oxide)	DERWENT;	
			IBM_TDB	
-	16	((((((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 12:04
		substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	
		conduct\$4))) and (first near2 oxide)) and ((silicon adj nitride)	EPO; JPO;	
		with (first near2 oxide))) and (second near2 oxide)) and	DERWENT;	
	L	etch\$4	IBM_TDB	

L Number	Hits	Search Text	DB	Time stamp
-	558920	capacitor	USPAT;	2004/02/06 11:50
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4784	capacitor and ((first adj conduct\$4) with substrate)	USPAT;	2004/02/06 11:51
			US-PGPUB;	
1			EPO; JPO;	
	ĺ		DERWENT;	
			IBM_TDB	
-	98978	capacitor and memory	USPAT;	2004/02/06 11:51
		·	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2639	(capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 11:51
		substrate)	US-PGPUB;	
		'	EPO; JPO;	
			DERWENT:	
			IBM_TDB	
-	167	((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 11:54
		substrate)) and ((silicon adj nitride) with (first adj conduct\$4))	US-PGPUB;	
,			EPO; JPO;	
	,		DERWENT;	
			IBM_TDB	
-	64	(((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 11:59
		substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	
		conduct\$4))) and (first near2 oxide)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	· 33	((((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 11:58
		substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	
		conduct\$4))) and (first near2 oxide)) and ((silicon adj nitride)	EPO; JPO;	
		with (first near2 oxide))	DERWENT;	
			IBM_TDB	
-	17	(((((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 12:00
		substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	
		conduct\$4))) and (first near2 oxide)) and ((silicon adj nitride)	EPO; JPO;	
		with (first near2 oxide))) and (second near2 oxide)	DERWENT;	
		, , , , , , , , , , , , , , , , , , ,	IBM_TDB	0004/00/00 40 6 :
J -	16	((((((capacitor and memory) and ((first adj conduct\$4) with	USPAT;	2004/02/06 12:04
[substrate)) and ((silicon adj nitride) with (first adj	US-PGPUB;	
[conduct\$4))) and (first near2 oxide)) and ((silicon adj nitride)	EPO; JPO;	
		with (first near2 oxide))) and (second near2 oxide)) and	DERWENT;	
		etch\$4	IBM_TDB 、	